AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-25 (cancelled)

26. (original) A semiconductor apparatus comprising:

a nonvolatile memory; and

a central processing unit,

wherein said nonvolatile memory has a plurality of memory cells,

wherein each of said memory cells includes:

a memory gate formed over a first semiconductor region with a first insulating film and a second insulating film interposed therebetween;

a first switch gate formed over said first semiconductor region to a first side of said memory gate with a third insulating film;

a second switch gate formed over the first semiconductor region to a second side of said memory gate with a fourth insulating film, wherein said second side is opposite said first side across said memory gate; and

a second semiconductor region and a third semiconductor region respectively formed adjacent to opposite sides of said first semiconductor region; and

wherein said first nonvolatile memory is capable of storing a program and data, and

wherein said central processing unit executes said program read from said first nonvolatile memory.

27. (original) A semiconductor apparatus according to claim 26, further comprising a random access memory,

wherein said random access memory is used for a work memory for said central processing unit.

28. (original) A semiconductor apparatus according to claim 27,

wherein said central processing unit controls to access to said nonvolatile memory.

29. (original) A semiconductor apparatus according to claim 28, wherein said nonvolatile memory is capable of rewriting data stored therein.

30. (original) A semiconductor apparatus according to claim 29, further comprising a second nonvolatile memory,

wherein said central processing unit controls to access to said second nonvolatile memory.

31. (original) A semiconductor apparatus according to claim 29, further comprising a communication circuit and an antenna,

wherein said communication circuit couples to said antenna, and

wherein said communication circuit is capable of communication by electromagnetic induction.

32. (original) A semiconductor apparatus according to claim 26,

wherein each said memory cell is capable of storing data by trapping electrons in said memory gate thereof to change a threshold voltage.